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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/836,144	04/17/2001	Hiroko Iwasaki	2271/50717-AY	7345	
75	590 06/15/2006		EXAM	EXAMINER	
RICHARD F. JAWORSKI			MCPHERSON, JOHN A		
Cooper & Dunham LLP 1185 Avenue of the Americas			ART UNIT	PAPER NUMBER	
New York, NY			1756		
			DATE MAILED: 06/15/2006	5	

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)				
	09/836,144	IWASAKI, HIROK	O			
Office Action Summary	Examiner	Art Unit				
	John A. McPherson	1756				
The MAILING DATE of this communication app Period for Reply	pears on the cover she	et with the correspondence ad	dress			
A SHORTENED STATUTORY PERIOD FOR REPLY WHICHEVER IS LONGER, FROM THE MAILING DATE of the strength of the may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. If NO period for reply is specified above, the maximum statutory period versiling to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMM 36(a). In no event, however, n will apply and will expire SIX (6 , cause the application to beco	UNICATION. nay a reply be timely filed) MONTHS from the mailing date of this come ABANDONED (35 U.S.C. § 133).				
Status						
1) Responsive to communication(s) filed on 03 A	pril 2006.					
2a) ☐ This action is FINAL . 2b) ☑ This	action is non-final.					
3) Since this application is in condition for allowar	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is					
closed in accordance with the practice under E	Ex parte Quayle, 1935	C.D. 11, 453 O.G. 213.				
Disposition of Claims						
4)⊠ Claim(s) <u>12 and 16-23</u> is/are pending in the application.						
4a) Of the above claim(s) is/are withdrawn from consideration.						
5) Claim(s) is/are allowed.						
6)⊠ Claim(s) <u>12 and 16-23</u> is/are rejected.						
7) Claim(s) is/are objected to.						
8) Claim(s) are subject to restriction and/o	r election requiremen	t.				
Application Papers						
9) The specification is objected to by the Examine	r.					
10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner.						
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).						
11)☐ The oath or declaration is objected to by the Ex	caminer. Note the atta	ched Office Action or form PT	O-152.			
Priority under 35 U.S.C. § 119						
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) Some * c) None of:						
1. Certified copies of the priority document						
2. Certified copies of the priority document3. Copies of the certified copies of the priority			Stage			
application from the International Bureau		Deen received in this National	Stage			
* See the attached detailed Office action for a list of the certified copies not received.						
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AMaahaa awaa						
Attachment(s) 1) Notice of References Cited (PTO-892)	4) Inter	view Summary (PTO-413)				
2) Notice of Draftsperson's Patent Drawing Review (PTO-948)	Pape	r No(s)/Mail Date				
 Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 	5) ∐ Notic 6) ☐ Othe	e of Informal Patent Application (PTC	D-152)			

DETAILED ACTION

Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 3/1/06 has been entered.

Response to Amendment

2. The Amendment filed 3/1/06 successfully overcomes the rejections set forth in paragraphs 2-4 and 6 of the Office Action mailed 11/3/05. Accordingly, these rejections are withdrawn.

Claim Rejections - 35 USC § 103

- 3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 12 and 16-21 are rejected under 35 U.S.C. 103(a) as being unpatentable over US 4,902,584 to Uchiyama et al. (Uchiyama). Uchiyama discloses an optical recording medium comprising a recording layer on a substrate and a protective layer,

wherein the protective layer comprises SiO₂, Si₃N₄ and a divalent metal oxide (such as MgO and ZnO), and optionally other members such as Al₂O₃ and AlN. The molar ratio of the silicon oxide to the silicon nitride ranges from about 50:50 to 90:10. See the abstract; column 4, lines 30-59; and Tables 2-4. It is the position of the Examiner that silicon nitride inherently has a thermal conductivity greater than or equal to 10W/m.deg when in the bulk state, because thermal conductivity in the bulk state is a material dependent property. Additionally, Uchiyama discloses the recoding layer may be made of a phase conversion type material. See column 6, lines 62 to column 7, line 17 and column 25, lines 3-4.

With respect to claims 18-21, it is the position of the Examiner that the statements "for use with the phase variation type data recording layer in a EFM modulation type recording system" and "for use with a recording mechanism which uses melting and rapid cooling of the phase variation type data recording layer" are statements of intended use for the claimed recording medium, and therefor do not provide a patentable distinction between the presently claimed recording medium layer and the recording medium of the applied prior art.

However, Uchiyama does not disclose providing a reflective layer in the phase variation type data recording medium.

The Examiner takes Official Notice that it is well known in the art to provide a reflective layer in a phase change optical recording medium, so as to provide the known benefits of increasing reflectivity and discharging heat. It would have been obvious to one skilled in the requisite art to provide a reflective layer in the optical recording

medium of Uchiyama because it is known in the art that a reflective layer increases reflectivity and assists in discharging heat in an optical recording medium of the phase change type.

4. Claims 12 and 16-23 rejected under 35 U.S.C. 103(a) as being unpatentable over US 4,902,584 to Uchiyama et al. (Uchiyama) in view of US 5,156,693 to Ide et al. [reference AE of the Information Disclosure Statement filed 4/17/01] (Ide). The disclosure of Uchiyama is discussed above in paragraph 3. However, with respect to claims 22 and 23, Uchiyama does not disclose a phase variation type recording layer substantially constituted by Ag, In, Sb and Te.

Ide discloses an information recording medium comprising heat resistant protective layers, a reflective layer which reflects light and/or discharges heat, and a recording layer which comprises a recording material of the composition AgInTeSb. See column 3, lines 3-16 and column 4, lines 32-40. It would have been obvious to one skilled in the requisite to utilize AgInTeSb, as taught by Ide, as the phase conversion type material in the optical recording medium of Uchiyama because it is taught that AgInTeSb is a phase-change type recording material which exhibits a long life expectancy, improved C/N and writing ratios, and improved writing and erasing sensitivities.

5. Claims 12, 16 and 18-23 are rejected under 35 U.S.C. 103(a) as being unpatentable over US 5,156,693 to Ide et al. [reference AE of the Information

Disclosure Statement filed 4/17/01] (Ide) in view of US 4,920,007 to Sawamura et al. (Sawamura). Ide discloses an information recording medium comprising a reflective layer and a recording layer which comprises a recording material of the composition AgInTeSb, wherein the recording medium further comprises protective layers made from various oxides (exemplified by SiO₂) nitrides (exemplified by Si₃N₄), sulfides, carbides, or mixtures thereof. See column 3, lines 3-16; column 4, lines 32-40; and column 4, line 63 to column 5, line 3. Furthermore, Ide discloses in Example 1 an optical disc comprising a substrate, a first heat resistant protective layer of Si₃N₄, a recording layer of Ag₁₁In₁₁Te₂₃Sb₅₅, a second heat resistant protective layer of Si₃N₄, and a reflecting layer. See column 5, lines 53 to 63.

With respect to claims 18-21, it is the position of the Examiner that the statements "for use with the phase variation type data recording layer in a EFM modulation type recording system" and "for use with a recording mechanism which uses melting and rapid cooling of the phase variation type data recording layer" are statements of intended use for the claimed recording medium, and therefor do not provide a patentable distinction between the presently claimed recording medium layer and the recording medium of the applied prior art.

However, Ide does not disclose utilizing a protective layer comprising silicon dioxide mixed with silicon nitride in a molar ratio of 10-85% silicon nitride.

Sawamura discloses an optical recording medium provided with a protective layer of an oxide-nitride mixture, wherein the oxide includes silicon oxide and the nitride includes silicon nitride. The nitride and oxide are mixed in a ratio of 9:1 to 1:9,

exemplified by a layer comprising Si₃N₄ and SiO₂ in weight proportions of 6:4. See the abstract; column 2, lines 48-51; column 3, lines 1-9; and Example 1. It is the position of the Examiner that silicon nitride inherently has a thermal conductivity greater than or equal to 10W/m.deg when in the bulk state, because thermal conductivity in the bulk state is a material dependent property. It would have been obvious to one skilled in the requisite art to utilize a mixture of Si₃N₄ and SiO₂, as taught by Sawamura, as the material of the protective layer in the recording medium of Ide because it is taught that such a protective layer provides for superior durability and adhesion as compared to oxides and nitrides alone.

Response to Arguments

6. Applicant's arguments filed 3/1/06 have been fully considered but they are not persuasive. With respect to the rejection over Uchiyama, Applicant argues that this reference does not disclose a phase variation type recording layer substantially constituted by Ag, In, Sb and Te. However, this limitation has been removed from independent claims 12 and 16 by the Amendment filed 3/1/06 (it is now present only in new dependent claims 22 and 23). Furthermore, while Uchiyama does not explicitly disclose providing a reflective layer, it is well known in the art to provide a reflective layer in a phase change optical recording medium. This is supported by the many phase change recording media references of record in the present application.

Additionally, Applicant argues that because Sawamura and Uchiyama are not concerned with the thermal effects within the recording media during recording, erasing

and overwriting, one skilled in the art would not have looked to modify the optical recording medium of Ide according to the teachings of Sawamura and Uchiyama regarding the constitution of the heat-resistant protective layer. However, the fact that Applicant has recognized another advantage which would flow naturally from following the suggestion of the prior art cannot be the basis for patentability when the differences would otherwise be obvious. See *Ex parte Obiaya*, 227 USPQ 58, 60 (Bd. Pat. App. & Inter. 1985).

7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to John A. McPherson whose telephone number is (571) 272-1386. The examiner can normally be reached on Monday through Friday, 8:00 AM to 4:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Mark Huff can be reached on (571) 272-1385. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a

USPTO Customer Service Representative or access to the automated information

system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

John A. McPherson Primary Examiner Art Unit 1756

JAM 6/7/06